

Sheet 1 of 2

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| Form 1449* | Atty. Docket No.: 303.678US4 | Serial No. Unknown |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) | Applicant: Kie Y. Ahn et al. | |
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| | Crowder, S., et al., "Trade-offs in the Integration of High Performance Devices with Trench Capacitor DRAM", <u>Die. Int. Electron Devices Meeting</u> , Washington, D.C., pp. 45-48, (Dec. 1997) |
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*Substitute Disclosure Statement Form (PTO-1449)

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